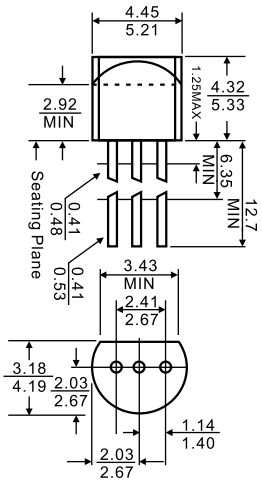
2SC2717(NPN)

TO-92 Bipolar Transistors

1. BASE
2. EMITTER
3. COLLECTOR

TO-92



Dimensions in inches and (millimeters)

Features

High Gain: G_{pe} =33 dB (Typ.) (f =45MH_Z)

Good Linearity of h_{FE}.

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55-125	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=12.5V,I_C=12.5mA	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=15mA,I_B=1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=15mA,I_B=1.5mA			1.5	V
Transition frequency	f_T	V_{CE}=12.5V,I_C=12.5mA	300			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=30MHz	0.8		2.0	pF
Collector-base time constant	$C_C{}^{.rbb'}$	V_{CB}=10V,I_E=-1mA,f=30MHz			25	ps
Power gain (fig.)	Gpe	V_{CC}=12.5V,I_E=-12.5mA,f=45MHz	28		36	dB

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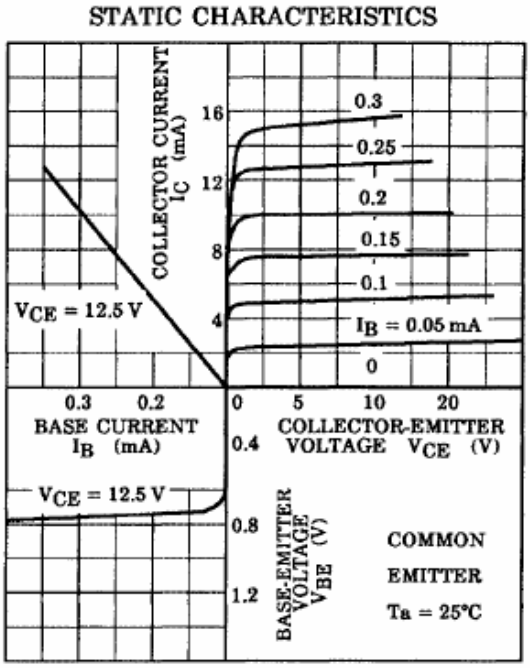
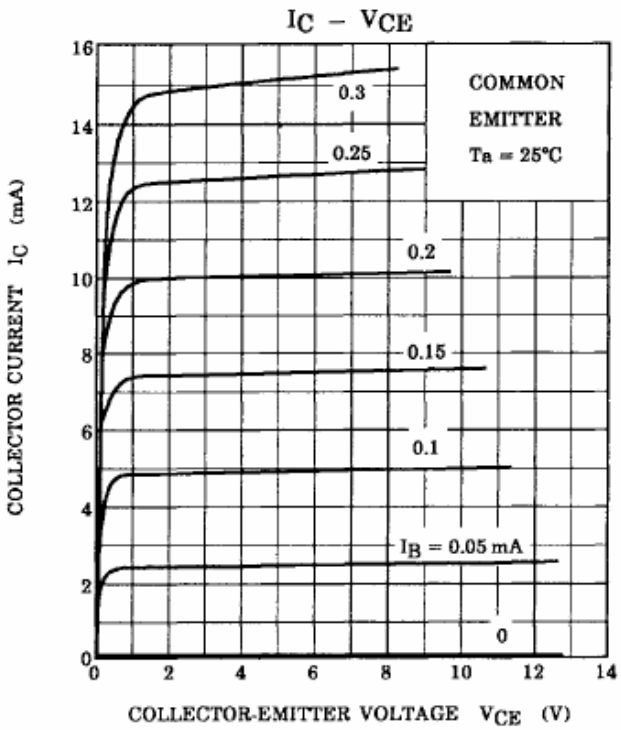
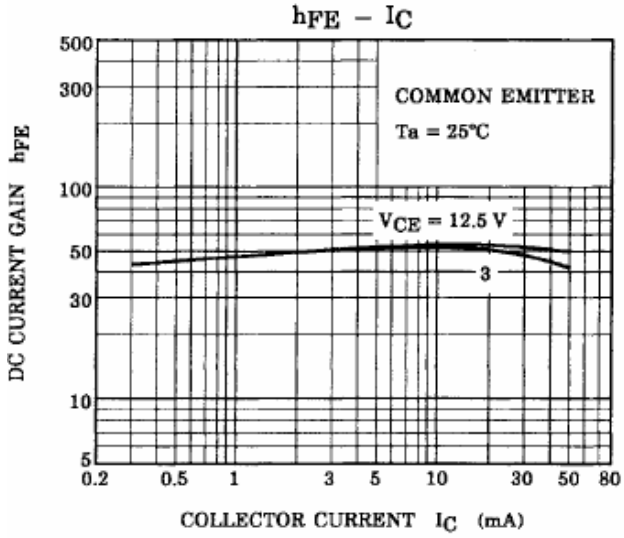
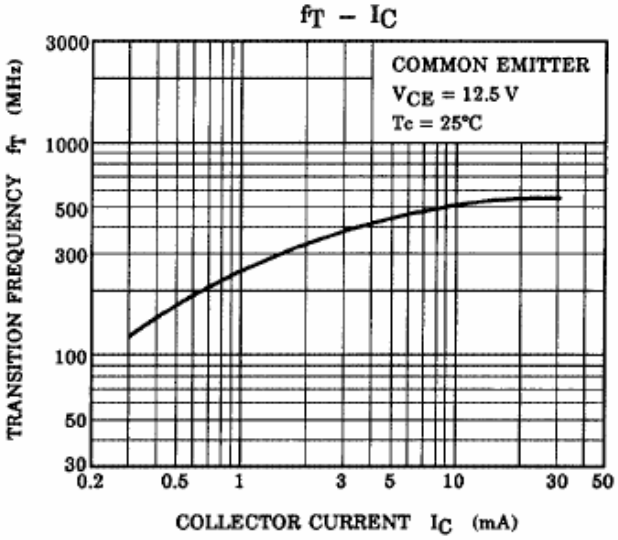
Typical Characteristics









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